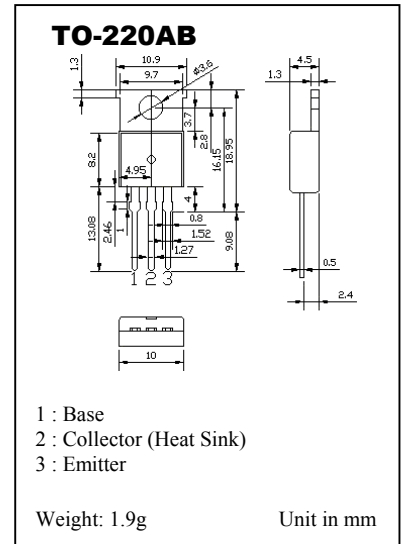


NPN EPITAXIAL SILICON DARLINGTON TRANSISTOR

...designed for use in horizontal output stages of video displays.

MAXIMUM RATINGS (T_c = 25 °C)

Characteristic	Symbol	Value	Unit
Collector Base Voltage	V _{CB0}	330	V
Collector Emitter Voltage	V _{CE0}	150	V
Emitter Base Voltage	V _{EB0}	6	V
Collector Current (DC)	I _C	8	A
Collector Current (Pulse)	I _{CP} *	15	A
Base Current	I _B	2	A
Collector Dissipation T _c = 25 °C	P _C	60	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 ~ 150	°C

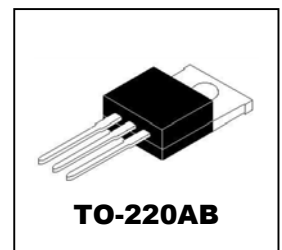


ELECTRICAL CHARACTERISTICS (T_c = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I _{CES}	V _{CE} = 330V, V _{BE} = 0	-	-	100	μA
Collector Cutoff Current	I _{CEV}	V _{CE} = 330V, V _{BE} = -6V	-	-	100	μA
Emitter Cutoff Current	I _{EBO}	V _{BE} = 6V, I _C = 0	-	-	3	mA
*Collector Emitter Saturation Voltage	V _{CE(sat)}	I _B = 50mA, I _C = 5A	-	-	1.5	V
*Base Emitter Saturation Voltage	V _{BE(sat)}	I _B = 50mA, I _C = 5A	-	-	2.4	V
*Collector Emitter Sustaining Voltage	V _{CE0(sus)}	I _B = 0, I _C = 100mA	150	-	-	V
*Damper Diode Forward Voltage	V _F	I _F = 4A	-	-	2	V

*Pulsed: pulsed duration = 300μs, duty cycle = 1.5%

**NPN EPITAXIAL
SILICON
DARLINGTON
TRANSISTOR**



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